



SERVICE BULLETIN

from: TRIO-KENWOOD COMMUNICATIONS, INC.

TR-7800, TR-7850

#861

SUBJECT: TR-7800, TR-7850 Memory Improvements

DATE 04/05/82

(Supercedes bulletins 829, 836, 841, 858)

TR-7800 & TR-7850 memory retention may be improved by the following changes on the Control and RX units.

Control unit X53-1180-xx

1. If not already present, add a $470k\Omega$ $\frac{1}{2}W$ resistor (RD14BB2B474J) (R54) on the foil side of the board from connector 11 UP line to ground. (Units before serial number 1110301)
2. If not already present, add a $470k\Omega$ $\frac{1}{2}W$ resistor (RD14BB2B474J) (R55) on the foil side of the board from connector 11 DOWN line to ground. (Units after serial number 1110101)
3. Hard-wire the two via holes (through holes without component leads installed) along the foil trace between Q18 pin 1 and L1.
4. Change D1 from an XZ-060 (6V, 5%) to a WZ-040 (V11-4102-50) (4V, 10%) Zener.
5. Check D3 for leakage, which would load the MB line voltage below its normal 5.2V DC setting.

RX unit X55-1270-xx

1. TR-7800; Change R94 from 56Ω $\frac{1}{2}W$ to 150Ω $\frac{1}{2}W$ (RD14CB2E151J)
2. TR-7850; Change R94 from 100Ω $\frac{1}{2}W$ to 150Ω $\frac{1}{2}W$ (RD14CB2E151J). This will reduce battery charge current to approximately 10 to 12 mA.
3. Cut the foil at the input to Q27, and connect Q27 input to the BB terminal. Connector 1 for constant battery charge at Power switch Off, and floating battery charge when using a TK-1 or BC-1 charger unit for memory back-up in base station operation.

